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Supporting information for

Intense-Pulsed-UV-Converted Perhydropolysilazane Gate Dielectrics for Organic Field-Effect Transistors and Logic Gates

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Figure S1. OM images of the PHPS films prepared at various number of intense pulses of the IPL irradiation as a function of electric field. The applied voltage was fixed to be 3.0 kV.



Figure S2. Current density of the PHPS films prepared at various number of intense pulses of the IPL irradiation as a function of electric field. The applied voltage was fixed to be 3.0 kV.



Figure S3. Top and cross-sectional SEM images of SiO₂ gate dielectric layer derived from PHPS by IPL.



Figure S4. Transfer characteristics of p-type pentacene (left) and n-type $PTCDI-C_8$ (right) OFETs with (a) the PHPS-derived SiO₂ films by thermal treatment (600 °C and 5 hours) and the commercial thermally-grown SiO₂.



Figure S5. Output characteristics of n-type PTCDI-C₈ OFETs with the PHPS-derived SiO₂ films by IPL irradiation (3.0 kV and 6,000 counts).